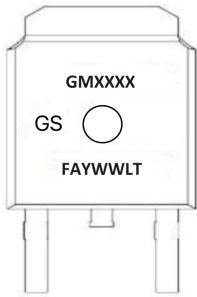
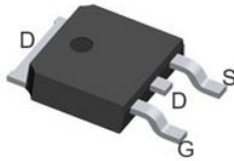


Product Summary

V_{DS} (V)	$R_{DS(on),max}$ (mΩ)	I_D (A)
30	4.7 @ $V_{GS} = 10V$	80 ⁽¹⁾

View and Internal Schematic Diagram



TO-252

NOTE:
 LOGO - GS
 GMXXXXX- Part number code
 F - Fab location code
 A - Assembly location code
 Y - Year code
 WW - Week code
 L&T - Assembly lot code

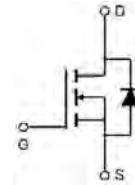
Features

- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Application

- Primary side switch
- Synchronous rectification
- DC/DC conversion
- Load switching
- Boost converters
- DC/AC inverters

Equivalent circuit



Absolute maximum rating@25°C

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	46	A
I_{DM}	Pulsed Drain Current ²	320	A
EAS	Single Pulse Avalanche Energy ³	282	mJ
I_{AS}	Avalanche Current	75	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	70	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristic

Parameter		Symbol	Max.	Unit
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	1.8	°C/W
Thermal resistance, junction-to-ambient ⁽⁴⁾	Steady state	$R_{\theta JA}$	50	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Static parameter						
Drain to source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0, I _D = 250 μA	30			V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.0	1.5	2.0	V
Gate-body leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		3.6	4.7	mΩ
	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 30 A		6.5	8.5	mΩ
Forward transconductance ⁽⁵⁾	g _{fs}	V _{DS} = 5 V, I _D = 30 A		28		S
Gate resistance	R _g	f = 1 MHz		1.0		Ω
Dynamic ⁽⁵⁾						
Total gate charge V _{GS} = 10V	Q _g	V _{DS} = 15 V, I _D = 30 A, V _{GS} = 10 V		39.2		nC
Gate-source charge	Q _{gs}			6		
Gate-drain charge	Q _{gd}			8.2		
Turn-on delay time	t _{d(on)}	V _{DS} = 15 V, I _D = 30 A, V _{GS} = 10 V, R _{GEN} = 2.9 Ω		22		ns
Rise time	t _r			26		
Turn-off delay time	t _{d(off)}			44		
Fall time	t _f			14		
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		1950		pF
Output capacitance	C _{oss}			220		
Reverse transfer capacitance	C _{rss}			165		
Diode Characteristics						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current ^{1,6}	I _S	V _G =V _S =0V , Force Current	---	---	80	A
Pulsed Source Current ^{2,6}	I _{SM}		---	---	320	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V , I _S =20A , T _J =25°C	---	---	1	V

Notes

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10sec.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.5mH,I_{AS}=75A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.Guaranteed by design, not subject to production testing.
- 6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

N- Channel Typical Characteristics

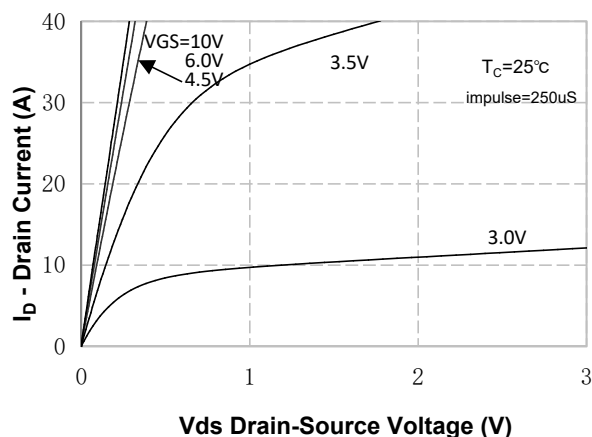


Figure 1. On-Region Characteristics

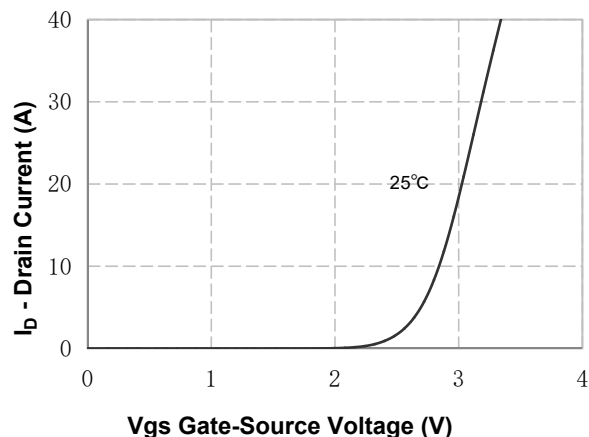


Figure 2. Transfer Characteristics

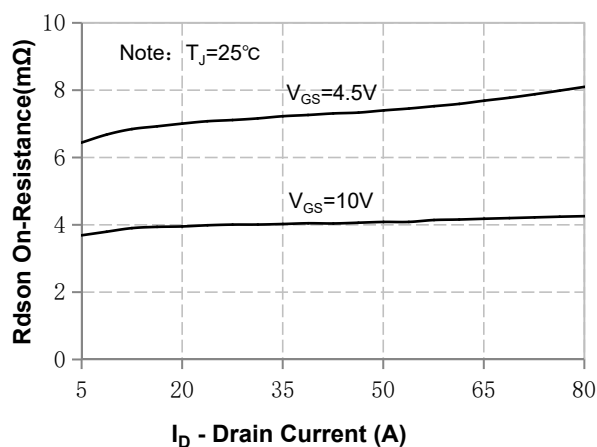


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

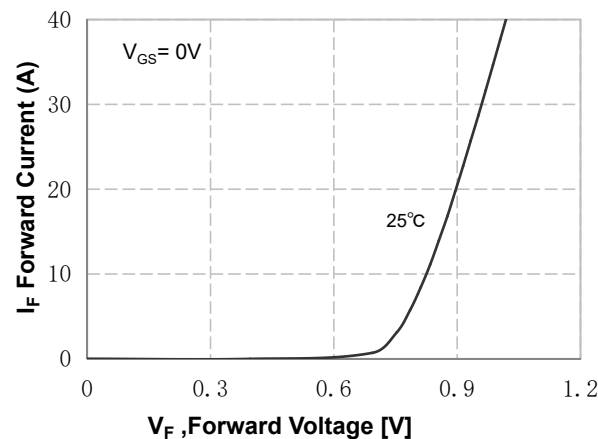


Figure 4. Body Diode Forward Voltage Variation vs Source Current

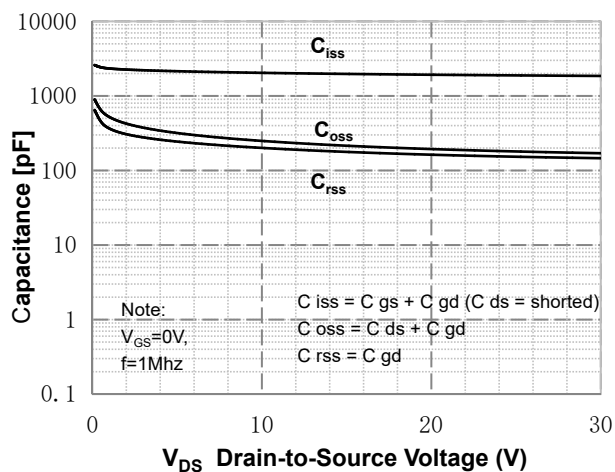


Figure 5. Capacitance Characteristics

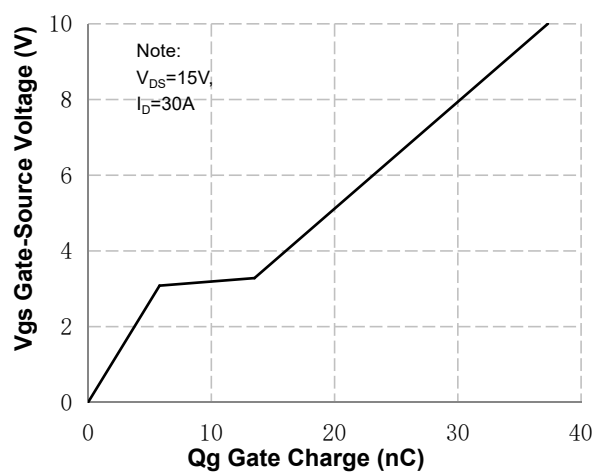


Figure 6. Gate Charge Characteristics

Typical Performance Characteristics

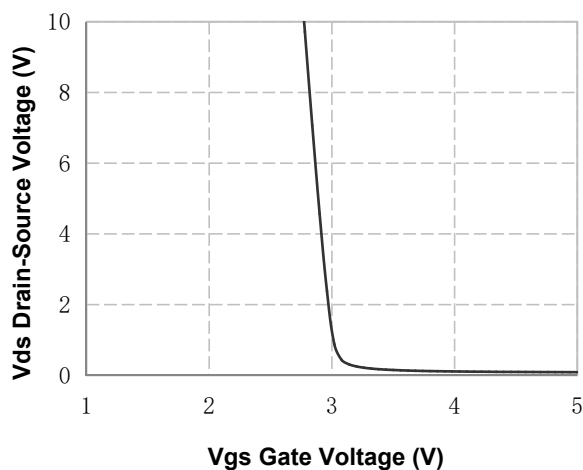


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

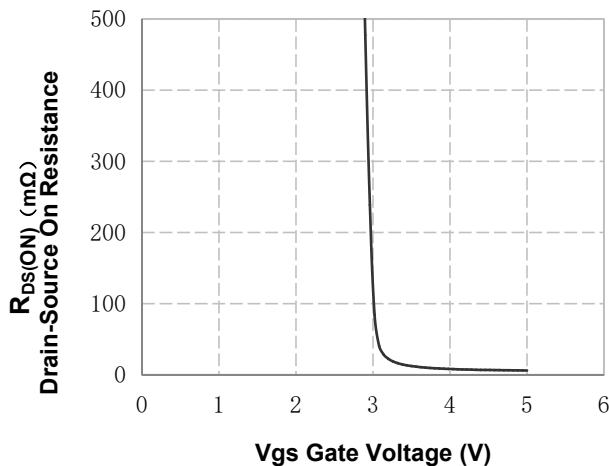


Figure 8. On-Resistance vs Gate Voltage

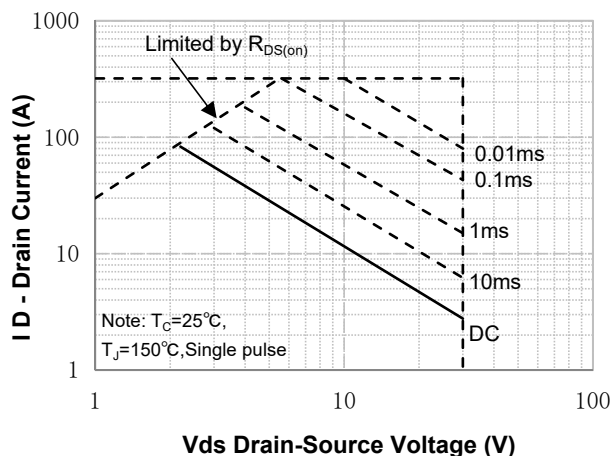


Figure 9. Maximum Safe Operating Area

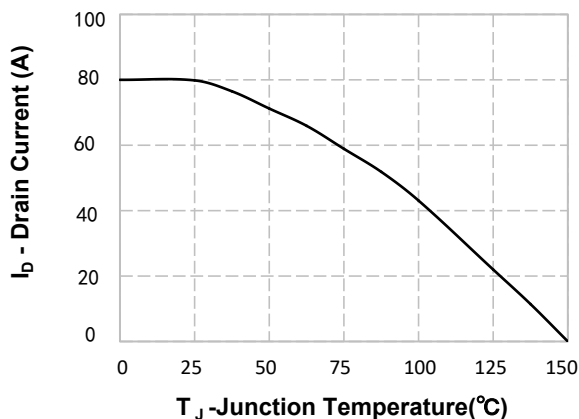


Figure 10. Maximum Continuous Drain Current vs Temperature

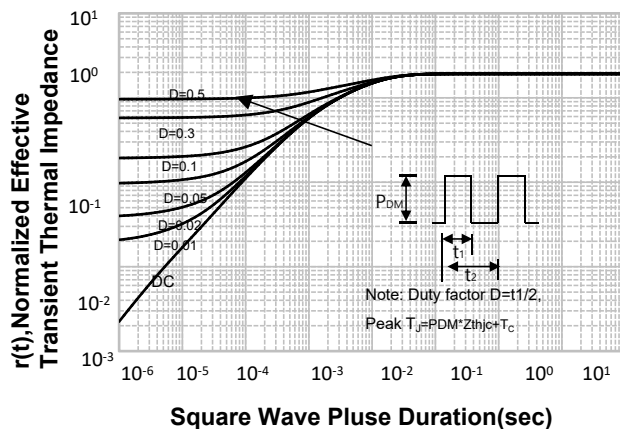
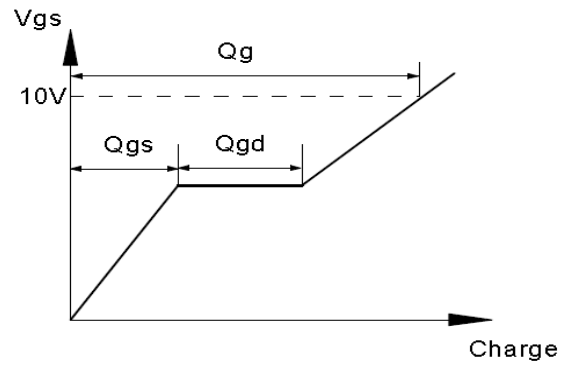
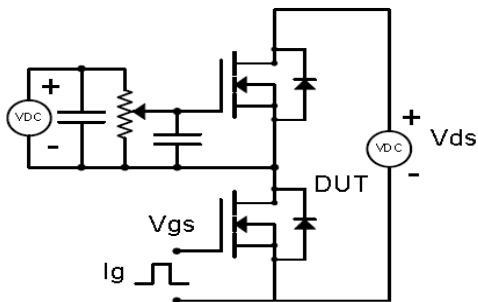


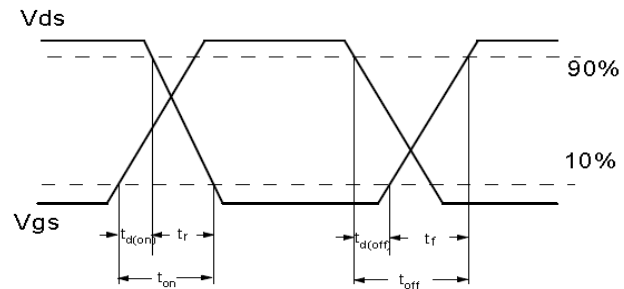
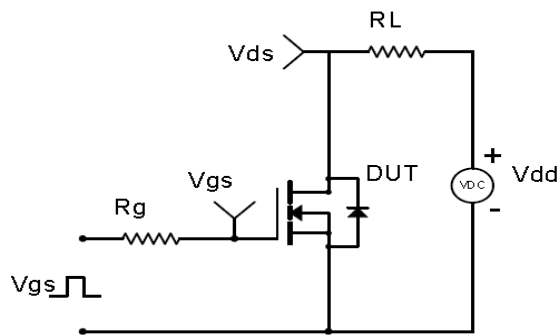
Figure 11. Transient Thermal Response Curve

Test Circuit & Waveform

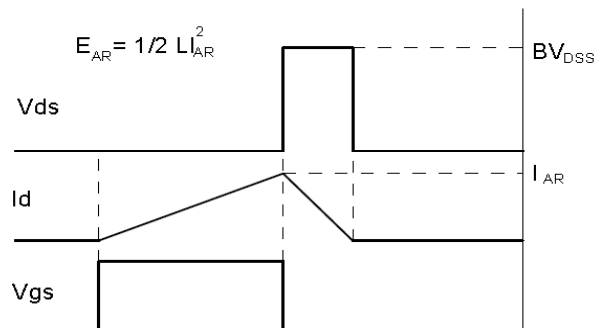
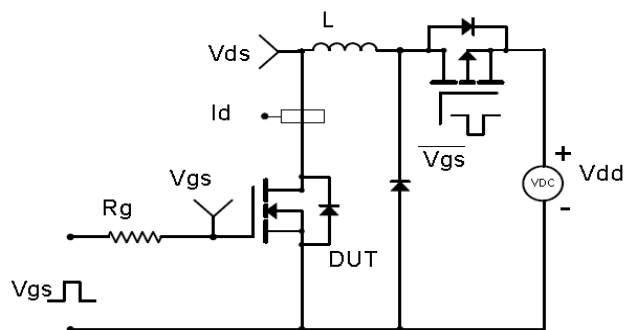
Gate Charge Test Circuit & Waveform



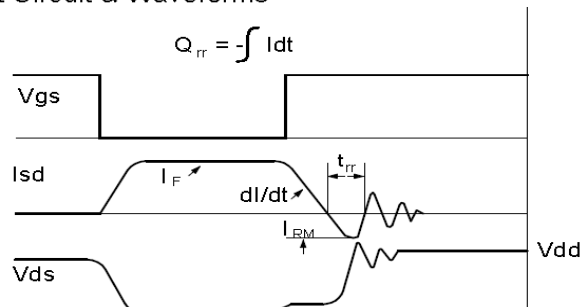
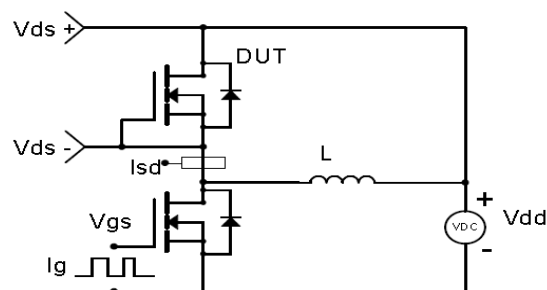
Resistive Switching Test Circuit & Waveforms



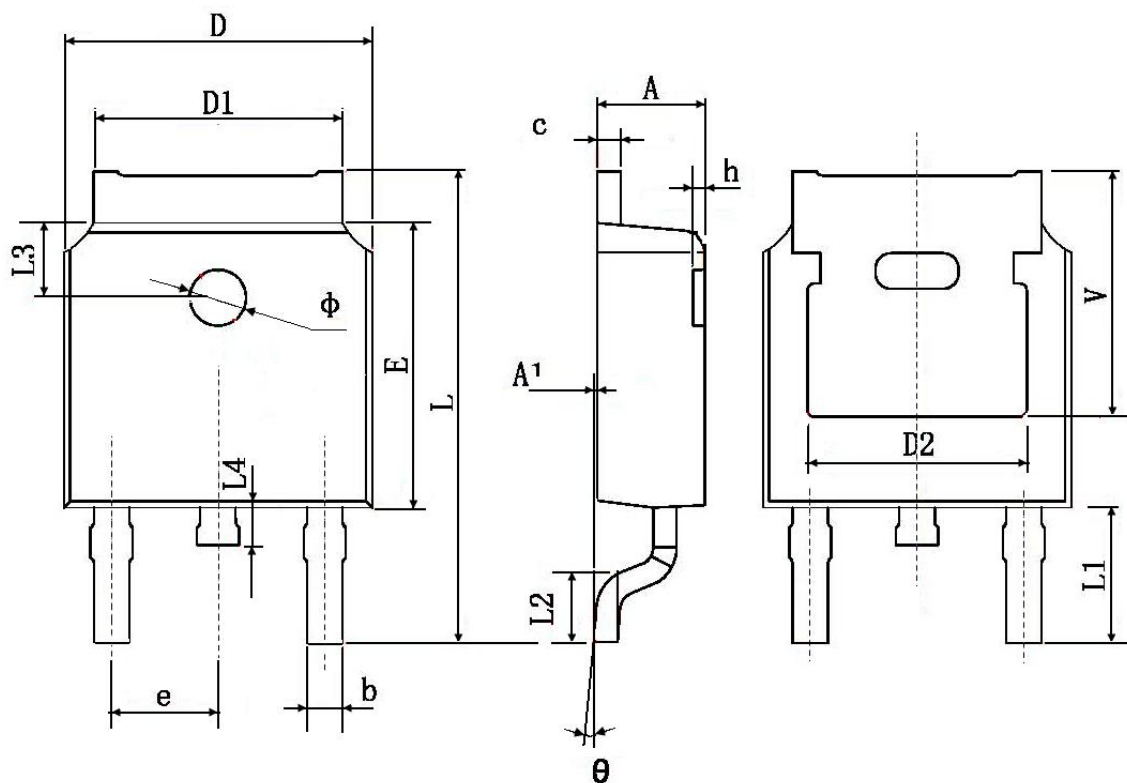
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Outline Drawing TO-252



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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